High quality epitaxial wafers

- **For laser diodes and light emitting devices**
  - Layer structure for Fabry-Perot lasers (quantum dot/quantum well) (quantum dot/well active layers with AlGaAs cladding layers)
  - Layer structure for DFB lasers (quantum dot/quantum well) (quantum dot/well active layers with bottom AlGaAs cladding layer)
  - VCSEL structure, DBR-incorporated structure

- **Application for photo-detection**
  - PIN photo-diode structure
  - Layers with quantum dots/wells

- **Electrical device applications**
  - Resonant Tunneling Diode structure
  - HEMT layer structure

- **Other custom structure (on an epitaxial substrate with InGaP layer can be possible)**

- **Base substrate**: 3-inch GaAs wafer
  (n-, p- or un-doped)

- **Wafers per batch**: 1~5 wafers

- **Possible grown layers**
  - GaAs
  - AlₓGa₁₋ₓAs (0 < x ≤ 1)
  - InAs quantum dots
  - InGaAs quantum dots
    (RT-PL wavelength : 1120 ~ 1290 nm)
  - InGaAs quantum wells (RT-PL wavelength : 1000 ~ 1160 nm)
  - For doping, n-type with Si or p-type with Be

- Original high-quality is approved via mass-productive 1.3-μm high-temperature data-com quantum dot lasers and short-pulse 1.06μm quantum well lasers for seed lasers for fiber lasers and various gas sensing.

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